EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	(advantage or benefit) with drain with (InSb or (indium adj antimonide))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/06 06:44
L2	6	("20050082522"|"20050285193"|"20060084235").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/06 06:44
L3	7725	InSb or (indium adj antimonide)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/06 06:45
L4	0	l2 and l3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/06 06:45
L5	8	((((diamond adj like) or (diamond-like) or (diamondlike)) adj (C or carbon)) or (diamond near2 carbon)) with source and (field adj effect adj transistor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/06 06:52
L6	16	(advantage or benefit) with ((amorphous adj carbon) or ((((diamond adj like) or (diamond-like) or (diamondlike)) adj (C or carbon)) or (diamond near2 carbon))) and (field adj effect adj transistor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/06 07:00
L7	5	((amorphous adj carbon) or ((((diamond adj like) or (diamond-like) or (diamondlike)) adj (C or carbon)) or (diamond near2 carbon))) with (material near2 source) and (field adj effect adj transistor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/06 07:59

EAST Search History

L8	943	(field adj effect adj transistor) and (channel with (si or silicon)) and (drain with (Ge or germanium))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/06 07:05
L9	155	(field adj effect adj transistor) and (channel with material with (si or silicon)) and (drain with material with (Ge or germanium))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/06 07:05
L10	105	(field adj effect adj transistor) and (channel with material with (si or silicon)) and (drain with material with (Ge or germanium)) and CMOS	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/06 07:06
L11	0	"propert$3 of" with ((amorphous adj carbon) or ((((diamond adj like) or (diamond-like) or (diamondlike)) adj (C or carbon)) or (diamond near2 carbon)))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/06 08:00
L12	2036	propert$3 with ((amorphous adj carbon) or ((((diamond adj like) or (diamond-like) or (diamondlike)) adj (C or carbon)) or (diamond near2 carbon)))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/06 08:03
L13	82	(electron adj affinity) with ((amorphous adj carbon) or ((((diamond adj like) or (diamond-like) or (diamondlike)) adj (C or carbon)) or (diamond near2 carbon)))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/06 08:03
S1	1	"10591863"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/24 20:08

EAST Search History

S2	1255	257/194.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/23 09:30
S3	1196	257/200.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/23 09:30
S4	455	257/201.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/23 09:31
S5	359	257/51.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/23 09:31
S6	406	257/183.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/23 09:31
S7	37	257/e29.068.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/23 09:31
S8	49	257/e29.079.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/23 09:31

EAST Search History

S9	348	257/e29.081.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/23 09:32
S10	9125	(material with channel) and (material with source) and (material with drain)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/23 09:33
S11	10	(((electron or electronic) near affinity) same (source or drain)) and ((increase or improve) with (transistor with operat$3))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/23 09:44
S12	837	(((electron or electronic) near affinity) same (source or drain))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/23 09:36
S13	6	(source near material) with (different) with (drain near material)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/23 09:49
S14	88	S10 and S12	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/23 09:50
S15	16	S10 and S12 and S2	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/23 10:11

EAST Search History

S16	85285	(PMOS or (p-channel) or (p adj channel)) and (NMOS or (n-channel) or (n adj channel)) with transistor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/23 10:13
S17	1	S2 and S12 and S16	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/23 10:14
S18	0	S3 and S12 and S16	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/23 10:14
S19	0	S4 and S12 and S16	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/23 10:14
S20	1	S5 and S12 and S16	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/23 10:15
S21	1	S6 and S12 and S16	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/23 10:16
S22	0	S7 and S12 and S16	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/23 10:16

EAST Search History

S23	0	S8 and S12 and S16	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/23 10:16
S24	1	S9 and S12 and S16	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/23 10:16
S25	24	("3263095" | "3283221" | "3708731" | "4163237" | "4424525").PN. OR ("4556895").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/10/23 10:18
S26	7	("4468851" | "4558337" | "4600932" | "4866490").PN. OR ("5986291"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/10/23 11:50
S27	137	(channel and source and drain) with (different near material)	US-PGPUB; USPAT; USOCR	OR	ON	2007/10/23 11:51
S28	50	S16 and S27	US-PGPUB; USPAT; USOCR	OR	ON	2007/10/23 12:28
S29	3	("20010020725"|"20040014276"|"6187641").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/10/23 12:40
S30	1	"6825506".pn.	US-PGPUB; USPAT; USOCR	OR	ON	2007/10/23 13:03
S31	5	"10364786"	US-PGPUB; USPAT; USOCR	OR	ON	2007/10/23 13:03
S32	9	((source near material) and (drain near material)) with different	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/24 09:31
S33	532	(electron adj affinity) with (si or silicon)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/24 09:32

S34	22	(electron adj affinity) with (SiGe or (silicon adj germanium))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/24 09:33
S35	18	S33 and S34	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/24 10:14
S36	103354	((increase or fast) with (switch$3 or operat$3)) and transistor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/24 10:21
S37	76	(source near material) with (drain near material)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/24 10:21
S38	5	S36 and S37	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/24 10:56
S39	0	"electron affinity of InGaAs"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/24 10:57
S40	2	"5326995".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/24 11:14

EAST Search History

S41	2	"20020190271"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/24 11:35
S42	2	"4903091".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/24 11:36
S43	2	"6414340".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/24 11:40
S44	9	((band or energy) adj diagram) same (InP and InGaAs) and (pnp or p-n-p)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/24 14:08
S45	0	(source near (GaAs or (gallium adj arsenide))) and (drain near (Ge or germanium)) and (channel near (si or silicon))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/24 14:10
S46	108	(source with (GaAs or (gallium adj arsenide))) and (drain with (Ge or germanium)) and (channel with (si or silicon))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/24 14:10
S47	210356	(field adj effect adj transistor) or (PMOS) or NMOS	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/24 14:11

S48	90	S46 and S47	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/24 14:36
S49	2	"20060244068"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/24 14:38
S50	2	"20070178650"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/31 17:01
S51	0	("2006/0244068").URPN.	USPAT	OR	ON	2007/10/24 15:00
S52	2	(((diamond-like or diamond) near (C or carbon)) with source) and ((germanium or Ge) with drain)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/24 20:10
S53	3	(((diamond-like or diamond) near (C or carbon)) with source) and ((GaAs or (gallium adj arsenide)) with drain)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/24 20:26
S54	2	(((diamond-like or diamond) near (C or carbon)) with source) and ((InSb or (indium adj antimonide)) with drain)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/24 20:28
S55	4	((GaAs or (gallium adj arsenide)) with source) and ((InSb or (indium adj antimonide)) with drain) and ((ge or germanium) with channel)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/24 20:34

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S56	1	(((diamond-like or diamond) near (C or carbon)) with source) and ((InSb or (indium adj antimonide)) with drain) and ((GaAs or (gallium adj arsenide)) with channel)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/24 20:36
S57	1	(((diamond-like or diamond) near (C or carbon)) with source) and ((ge or germanium) with drain) and ((GaAs or (gallium adj arsenide)) with channel)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/24 20:37
S58	141	((si or silicon) with source) and ((ge or germanium) with drain) and ((GaAs or (gallium adj arsenide)) with channel)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/24 20:42
S59	11	((si or silicon) with source) and ((InSb or (indium adj antimonide)) with drain) and ((GaAs or (gallium adj arsenide)) with channel)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/24 20:38
S60	74101	(channel with (Si or silicon))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/31 16:03
S61	88924	source with (((diamond-like or diamond) adj C) or carbon)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/31 16:13
S62	4290	drain with (Ge or germanium)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/31 16:05

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S63	34	drain with (InSb or (indium adj antimonide))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/31 16:08
S64	186	S60 and S61 and S62	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/31 16:08
S65	522	source with ((diamond-like or diamond) adj (C or carbon))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/31 16:32
S66	2	S60 and S62 and S65	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/31 16:16
S67	8694	channel with (Ge or germanium)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/31 16:16
S68	139628	source with (Si or silicon)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/31 16:17
S69	8716	source with (GaAs or (gallium adj arsenide))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/31 16:17

S70	5	S67 and S68 and S63	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/31 16:22
S71	4	S67 and S69 and S63	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/31 16:22
S72	980	source with (((diamond-like or (diamond adj like)) adj (C or carbon)) or DLC)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/31 16:34
S73	2	S60 and S62 and S72	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/31 16:35
S74	1	S67 and S63 and S72	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/31 16:35
S75	4	("20040256700"|"20050045995"). PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/31 17:04
S76	8	("20040031996"|"20050184345"|"20060043498"|"20060258072").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/31 17:04
S77	0	("2006/0043498").URPN.	USPAT	OR	ON	2007/10/31 17:16

S78	7	("5849440"|"5858830"|"6103020"|"6197632"|"6541382"|"6605498"|"6621131").PN.	USPAT	OR	ON	2007/10/31 17:19
S79	0	("20040061191"|"20050287752").PN.	USPAT	OR	ON	2007/10/31 17:19
S80	0	("20040084735").PN.	USPAT	OR	ON	2007/10/31 17:20
S81	7964	asymmetr$4 with (device or transistor)	USPAT	OR	ON	2007/10/31 17:21
S82	941	(improve or increase) with (carrier adj mobility)	USPAT	OR	ON	2007/10/31 17:22
S83	28	S81 and S82	USPAT	OR	ON	2007/10/31 17:22
S84	2	"5801401".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/05 11:01
S85	1	(impact adj ionization) and kumashiro and shigetaka and (electron adj affinity)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/05 11:27
S86	8713	channel with (Ge or germanium)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/05 11:27
S87	8713	S86 and S86	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/05 11:27
S88	34	drain with (InSb or (indium adj antimonide))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/05 11:27

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S89	5	S88 and S86	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/05 11:29
S90	74203	channel with (Si or silicon)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/05 11:29
S91	4304	drain with (Ge or germanium)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/05 11:30
S92	5	source with (diamond-like adj C)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/05 11:33
S93	0	("2007/0210301").URPN.	USPAT	OR	ON	2007/11/05 12:01
S94	4229	source with (GaAs or (gallium adj arsenide))	USPAT	OR	ON	2007/11/05 12:01
S95	7	S88 and S94	USPAT	OR	ON	2007/11/05 12:05
S96	6	(upper adj level) with (valence adj band)	USPAT	OR	ON	2007/11/05 12:09
S97	103	(valence adj band) with (InP or (indium adj phosphide))	USPAT	OR	ON	2007/11/05 13:29
S98	34	(valence adj band) with ((InP or (indium adj phosphide)) and (InGaAs or (indium adj gallium adj arsenide)))	USPAT	OR	ON	2007/11/05 13:55
S99	0	"194370".pn.	USPAT	OR	ON	2007/11/05 13:56
S100	1	"4893155".pn.	USPAT	OR	ON	2007/11/05 14:26
S101	7	(((band or energy) adj gap) with (InGaAs or (indium adj gallium adj arsenide))) and ((electron adj affinity) with (InGaAs or (indium adj gallium adj arsenide)))	USPAT	OR	ON	2007/11/05 16:55

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S10 2	0	"11786210"	USPAT	OR	ON	2007/11/05 16:55
S10 3	0	"10786210"	USPAT	OR	ON	2007/11/05 16:56
S10 4	1	"5739558".pn.	USPAT	OR	ON	2007/11/05 17:34
S10 5	613	(common or usual) with drain with material	USPAT	OR	ON	2007/11/05 17:35
S10 6	208	((common or usual) with drain with material) and (field adj effect adj transistor)	USPAT	OR	ON	2007/11/05 17:35